



Date Mailed: April 18, 2006

Sheet 1 of 1

<b>FORM 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b>  <b>IN AN APPLICATION</b> (Use several sheets if necessary)	<b>Docket Number:</b> 10873.1623USWO	<b>Application Number:</b> 10/522,488
	<b>Applicant:</b> SASAKI, et al.	
	<b>Filing Date:</b> January 26, 2005	<b>Group Art Unit:</b> 2811

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EXAMINER	/Robert Kunemund/	DATE CONSIDERED	02/05/2007
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.			

\*Substitute Disclosure Statement Form (PTO-1449)

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PAGE 4/16 \* RCVD AT 4/18/2006 4:44:49 PM [Eastern Daylight Time] \* SVR:USPTO-EFXRF-3/17 \* DNUS:2738300 \* CSID:612-455-3801 \* DURATION (mm:ss):05:28

FORM 1449\*

## INFORMATION DISCLOSURE STATEMENT

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Docket Number:

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
RK	5,868,837	02/1999	DiSalvo et al.			
RK	6,001,748	12/1999	Tanaka et al.			
RK	6,270,569	08/2001	Shibata et al.			
RK	2002/0046695	04/2002	Sarayama et al.			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
RK	0 811 708	12/1997	Europe				
RK	1288079	03/2001	China			Abstract	
RK	01/24921	04/2001	WIPO				
RK	1 278 233	01/2003	Europe				

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

RK		Grzegory et al., "III-V Nitrides-Thermodynamics and Crystal Growth at High N <sub>2</sub> Pressure", Journal of Physics and Chemistry of Solids (1995); 56: 639-647
RK		Song et al., "Bulk GaN single crystals: growth conditions by flux method", Journal of Crystal Growth (2003); 247: 275-278
RK		Morishita et al., "Growth of bulk GaN single crystals in metal-sodium flux system", Journal of Japanese Association for Crystal Growth (2002); 29: 119-120
RK		Extended Abstracts (The 63rd Autumn Meeting, 2002); The Japan Society of Applied Physics No. 0 and No. 1
RK		Proceedings of the 47th Symposium of Synthetic Crystals, "LPE growth of GaN single crystal and LPE growth using Na-Ca-mixed flux", pp. 87-88
RK		Kawamura et al., "Synthesis of Bulk GaN Single Crystals Using Na-Ca Flux", Japanese Journal of Applied Physics (2002); 41: 1440-1442

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